

RSQ015N06FRA

Nch 60V 1.5A Power MOSFET

V_{DSS}	60V
R _{DS(on)} (Max.)	290mΩ
I _D	1.5A
P_{D}	1.25W

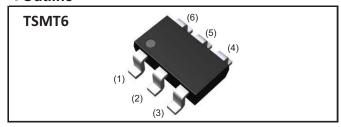
Features

- 1) Low on resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (TSMT6).
- 4) Pb-free lead plating; RoHS compliant
- 5) AEC-Q101 Qualified

Application

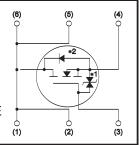
DC/DC converters

Outline



•Inner circuit

- (1) Drain
- (2) Drain
- (3) Gate
- (4) Source
- (5) Drain
- (6) Drain
- *1 ESD PROTECTION DIODE
- *2 BODY DIODE



Packaging specifications

	Packaging	Taping
	Reel size (mm)	180
Type	Tape width (mm)	8
Туре	Basic ordering unit (pcs)	3,000
	Taping code	TR
	Marking	PX

● Absolute maximum ratings(T_a = 25°C)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	60	V
Continuous drain current	I _D *1	±1.5	А
Pulsed drain current	I _{D,pulse} *2	±6	А
Gate - Source voltage	V_{GSS}	±20	V
Dower discination	P _D *3	1.25	W
Power dissipation	P _D *4	0.6	W
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	-55 to +150	°C

●Thermal resistance

Parameter	Symbol	Values			Unit
raiametei	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - ambient	R _{thJA} *3	-	-	100	°C/W
Thermal resistance, junction - ambient	R _{thJA} *4	-	-	208	°C/W

•Electrical characteristics($T_a = 25$ °C)

Parameter	Symbol	Conditions	Values			Unit	
r al allietei	Symbol	e di		Min. Typ.		Offic	
Drain - Source breakdown voltage	V _{(BR)DSS}	$V_{GS} = 0V$, $I_D = 1mA$	60	-	-	V	
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_{j}}$	I _D = 1mA referenced to 25°C	-	67	-	mV/°C	
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 60V, V_{GS} = 0V$	-	-	1	μА	
Gate - Source leakage current	I _{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±10	μА	
Gate threshold voltage	V _{GS (th)}	$V_{DS} = 10V$, $I_D = 1mA$	1.0	-	2.5	V	
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{(GS)th}}{\Delta T_{j}}$	I _D = 1mA referenced to 25°C	-	-4.4	-	mV/°C	
	_ *5	V _{GS} =10V, I _D =1.5A	-	210	290		
Static drain - source		V _{GS} =4.5V, I _D =1.5A	-	240	330	C	
on - state resistance	$R_{DS(on)}$	V _{GS} =4V, I _D =1.5A	-	255	350	mΩ	
		V _{GS} =10V, I _D =1.5A, T _j =125°C	-	360	510		
Gate input resistannce	R _G	f = 1MHz, open drain	-	10	-	Ω	
Transconductance	g _{fs} *5	$V_{DS} = 10V, I_{D} = 1.5A$	1.0	2.4	-	S	

^{*1} Limited only by maximum temperature allowed.

^{*2} Pw \leq 10 μ s, Duty cycle \leq 1%

^{*3} Mounted on a seramic board (30×30×0.8mm)

^{*4} Mounted on a FR4 (15×20×0.8mm)

•Electrical characteristics($T_a = 25$ °C)

Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol Conditions -		Min.	Тур.	Max.	Offic
Input capacitance	C _{iss}	V _{GS} = 0V	-	110	-	
Output capacitance	C _{oss}	V _{DS} = 10V	-	28	-	pF
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	12	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \simeq 30V, V_{GS} = 10V$	-	6	-	
Rise time	t _r *5	I _D = 0.7A	-	9	-	no
Turn - off delay time	t _{d(off)} *5	$R_L = 42.8\Omega$	-	15	-	ns
Fall time	t _f *5	$R_G = 10\Omega$	-	10	-	

•Gate Charge characteristics($T_a = 25$ °C)

Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	Q _g *5	$V_{DD} \simeq 30V$, $I_D = 1.5A$ $V_{GS} = 5V$	-	2	-	
Total gate charge		$V_{DD} \simeq 30V, I_{D} = 1.5A$ $V_{GS} = 10V$	-	3.5	-	nC
Gate - Source charge		$V_{DD} \simeq 30V, I_{D} = 1.5A$ $V_{GS} = 5V$	-	0.8	-	
Gate - Drain charge	Q _{gd} *5	$V_{GS} = 5V$	-	0.5	-	

●Body diode electrical characteristics (Source-Drain)(T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l _S *1	T _a = 25°C	-	-	1	А
Forward voltage	V _{SD} *5	$V_{GS} = 0V, I_{S} = 1.5A$	-	-	1.2	V

^{*5} Pulsed

•Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

120
100
80
40
40
20
0 50 100 150 200

Junction Temperature : Tj [°C]

Fig.2 Maximum Safe Operating Area $P_W = 1 ms$ $P_{W} = 100 \mu s$ Drain Current: -I_D [A] 1 Operation in this area is limited by R_{DS}(on) $(V_{GS} = 10V)$ DC Operation 0.1 $P_W = 10ms$ T_a=25°C Single Pulse Mounted on a ceramic board. $(30mm \times 30mm \times 0.8mm)$ 0.01 0.1 10 100

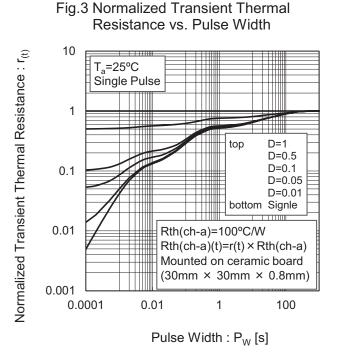
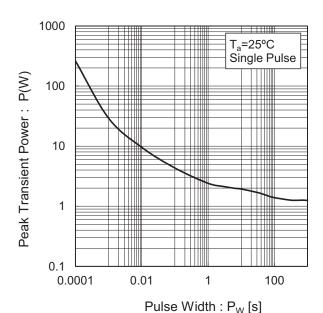


Fig.4 Single Pulse Maxmum Power dissipation

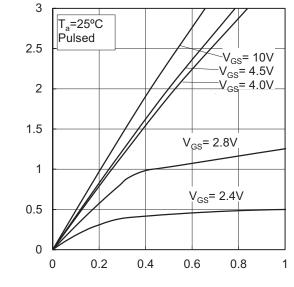
Drain - Source Voltage: V_{DS} [V]



Drain Current: -I_D [A]

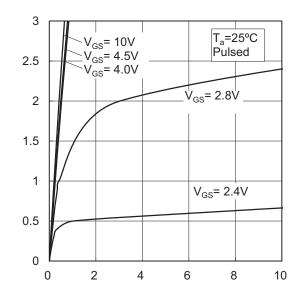
•Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)



Drain - Source Voltage : -V_{DS} [V]

Fig.6 Typical Output Characteristics(II)



Drain - Source Voltage : -V_{DS} [V]

Avalanche Energy: E_{AS} / E_{AS} max. [%]

3

•Electrical characteristic curves

Fig.7 Breakdown Voltage vs. Junction Temperature Drain - Source Breakdown Voltage: V_{(BR)DSS} [V] 120 V_{GS}=0V $I_D = 1 \text{mA}$ pulsed 90 60 30 0 -50 0 50 100 150 Junction Temperature : T_i [°C]

1

0.001

0

Gate - Source Voltage : V_{GS} [V]

Fig.9 Gate Threshold Voltage vs. Junction Temperature 2.5 V_{DS}=10V Gate Threshold Voltage: V_{GS(th)} [V] $I_D = 1 \text{mA}$ 2 pulsed 1.5 1 0.5 0 0 50 100 -50 150 Junction Temperature : T_i [°C]

10
V_{DS}= 10V
Pulsed
T_a= -25°C
T_a=25°C
T_a=75°C
T_a=125°C
T_a=125°C

Drain Current: I_D [A]

Fig.10 Transconductance vs. Drain Current

Fransconductance: gfs [S]

•Electrical characteristic curves

Fig.11 Drain CurrentDerating Curve

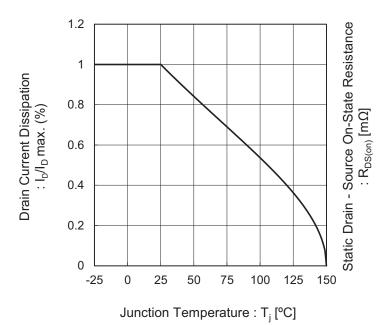
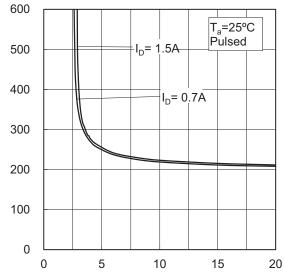


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



Gate - Source Voltage : V_{GS} [V]

Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(I)

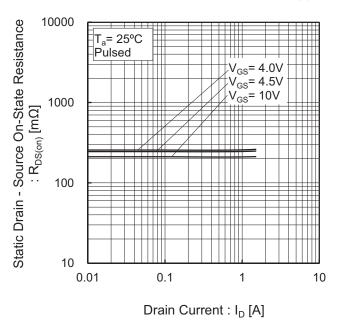
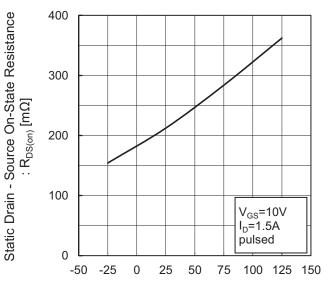


Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature



Junction Temperature : T_i [°C]

• Electrical characteristic curves

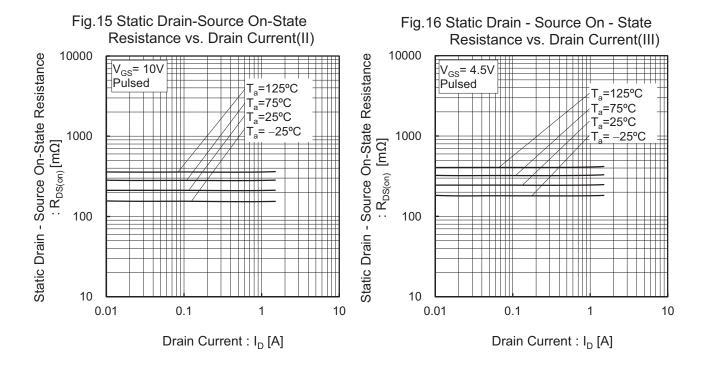
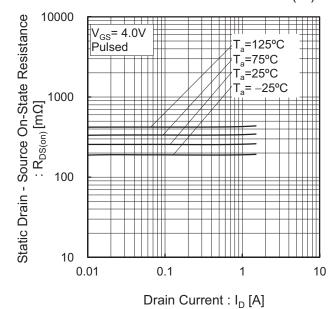


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV)



Capacitance: C [pF]

Gate - Source Voltage : V_{GS} [V]

•Electrical characteristic curves

T_a=25°C f=1MHz

0.01

s=0V

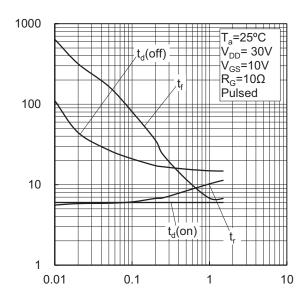
Fig.18 Typical Capacitance vs. Drain - Source Voltage 1000 Ciss Switching Time: t [ns] 100 10 Coss

Drain - Source Voltage : V_{DS} [V]

10

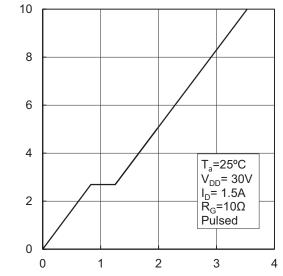
100

Fig.19 Switching Characteristics



Drain Current: I_D [A]

Fig.20 Dynamic Input Characteristics



Total Gate Charge : Q_g [nC]

vs. Source Drain Voltage 10 V_{GS}=0V Pulsed 1 T_a=125°C 0.1 T_a=25°C T_a= -25°C

Fig.21 Source Current

Source-Drain Voltage: V_{SD} [V]

0.5

Source Current: I_S [A]

0.01

0

1.5

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

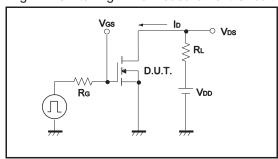


Fig.2-1 Gate Charge Measurement Circuit

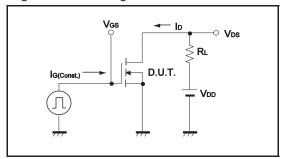


Fig.1-2 Switching Waveforms

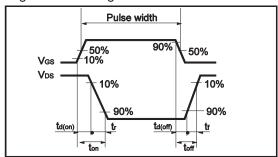
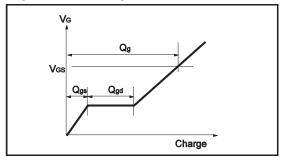
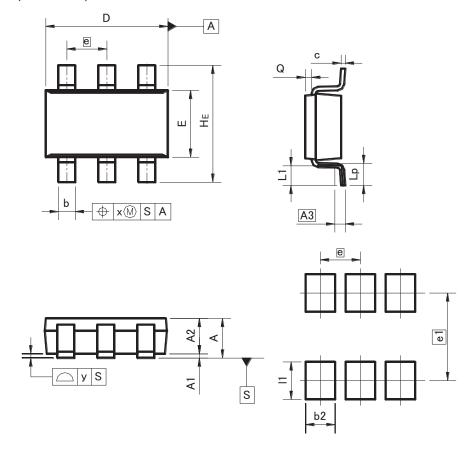


Fig.2-2 Gate Charge Waveform



●Dimensions (Unit:mm)





Patterm of terminal position areas

DIM	MILIMI	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	-	1.00	-	0.039	
A1	0.00	0.10	0	0.004	
A2	0.75	0.95	0.03	0.037	
A3	0.3	25	0.0	01	
b	0.35	0.50	0.014	0.02	
С	0.10	0.26	0.004	0.01	
D	2.80	3.00	0.11	0.118	
E	1.50	1.80	0.059	0.071	
е	0.9	95	0.0	04	
HE	2.60	3.00	0.102	0.118	
L1	0.30	0.60	0.012	0.024	
Lp	0.40	0.70	0.016	0.028	
Q	0.05	0.25	0.002	0.01	
Х	_	0.20	_	0.008	
У	_	0.10	_	0.004	

DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
e1	2.10		0.08		
b2		0.70	ı	0.028	
11	-	0.90	-	0.035	

Dimension in mm/inches

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ĺ	JAPAN	USA	FU	CHINA
	CLASSII		CLASS II b	• • • • • • • • • • • • • • • • • • • •
	CLASSIV	CLASSⅢ	CLASSⅢ	CLASSⅢ

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 - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
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 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

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- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
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 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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